

ISC Silicon NPN Power Transistor

DESCRIPTION

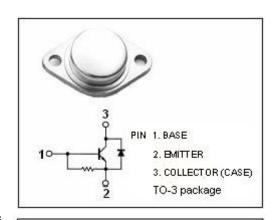
- · High Breakdown Voltage-
 - : V_{CES}= 1700V (Min)
- Built-in Damper Didoe
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

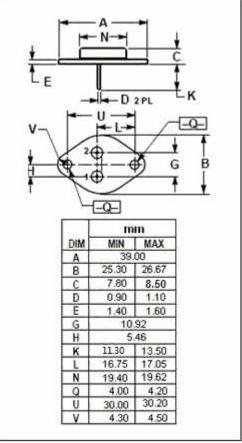
APPLICATIONS

• Designed for high voltage, high power switching applications.



SYMBOL	PARAMETER	VALUE	UNIT
V _{CES}	Collector-Emitter Voltage	1700	V
V _{EBO}	Emitter-Base Voltage	6	V
lc	Collector Current- Continuous	8	А
Pc	Collector Power Dissipation @ Tc=25℃	50	W
Тл	Junction Temperature	150	$^{\circ}$ C
T _{stg}	Storage Temperature Range	-45~150	${\mathbb C}$







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2SC3659

ELECTRICAL CHARACTERISTICS

Tc=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 1.25A			2.0	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 5A; I _B = 1.25A			1.5	V
Ісво	Collector Cutoff Current	V _{CE} = 1400V; I _E = 0			0.5	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 6V; I _C = 0			500	mA
V _{ECF}	C-E Diode Forward Voltage	I _F = 6A			2.0	V
t _f	Fall Time	I _C = 5A, I _{B1} = 1A, I _{B2} = -2.5A, L _B = 0			0.5	μ \$

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